













# 6-Pin DIP Optoisolators Transistor Output

The 4N35, 4N36 and 4N37 devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector.

- Current Transfer Ratio 100% Minimum @ Specified Conditions
- · Guaranteed Switching Speeds
- · Meets or Exceeds all JEDEC Registered Specifications
- To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.

### **Applications**

- General Purpose Switching Circuits
- · Interfacing and coupling systems of different potentials and impedances
- · Regulation Feedback Circuits
- Monitor & Detection Circuits
- Solid State Relays

### **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Value	Unit		
٧R	6	Volts		
ΙF	60	mA		
PD	120	mW		
	1.41	mW/°C		
OUTPUT TRANSISTOR				
	V <sub>R</sub>	V <sub>R</sub> 6  I <sub>F</sub> 60  P <sub>D</sub> 120		

Collector–Emitter Voltage	VCEO	30	Volts
Emitter-Base Voltage	V <sub>EBO</sub>	7	Volts
Collector–Base Voltage	V <sub>СВО</sub>	70	Volts
Collector Current — Continuous	IC	150	mA
Detector Power Dissipation @ T <sub>A</sub> = 25°C with Negligible Power in Input LED	PD	150	mW
Derate above 25°C		1.76	mW/°C

### **TOTAL DEVICE**

Isolation Source Voltage <sup>(1)</sup> (Peak ac Voltage, 60 Hz, 1 sec Duration)	VISO	7500	Vac(pk)
Total Device Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	250 2.94	mW mW/°C
Ambient Operating Temperature Range <sup>(2)</sup>	TA	-55 to +100	°C
Storage Temperature Range(2)	T <sub>stg</sub>	-55 to +150	°C
Soldering Temperature (10 sec, 1/16" from case)	TL	260	°C

- 1. Isolation surge voltage is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.
- 2. Refer to Quality and Reliability Section in Opto Data Book for information on test conditions.

Preferred devices are Motorola recommended choices for future use and best overall value.

GlobalOptoisolator is a trademark of Motorola, Inc.

## 4N35\*

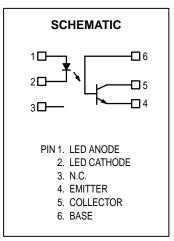
**4N36** 

**4N37** 

[CTR = 100% Min]

\*Motorola Preferred Device







### 4N35 4N36 4N37

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)(1)

Characteristic		Symbol	Min	Тур(1)	Max	Unit	
INPUT LED			•	•			•
Forward Voltage (I <sub>F</sub> =	10 mA)	T <sub>A</sub> = 25°C T <sub>A</sub> = -55°C T <sub>A</sub> = 100°C	VF	0.8 0.9 0.7	1.15 1.3 1.05	1.5 1.7 1.4	V
Reverse Leakage Cur	rent (V <sub>R</sub> = 6 V)		I <sub>R</sub>	_	_	10	μΑ
Capacitance (V = 0 V,	f = 1 MHz)		СЈ	_	18	_	pF
OUTPUT TRANSISTOR							
Collector–Emitter Dark	Current ( $V_{CE} = 10 \text{ V}, T_{A} = 2$ ( $V_{CE} = 30 \text{ V}, T_{A} = 1$		ICEO	_ _	1 —	50 500	nA μA
Collector–Base Dark Current ( $V_{CB} = 10 \text{ V}$ ) $T_{A} = 25^{\circ}\text{C}$ $T_{A} = 100^{\circ}\text{C}$			ICBO	_	0.2 100	20 —	nA
Collector–Emitter Brea	akdown Voltage (I <sub>C</sub> = 1 mA)		V(BR)CEO	30	45	_	V
Collector-Base Break	down Voltage (I <sub>C</sub> = 100 μA)		V(BR)CBO	70	100	_	V
Emitter-Base Breakdo	wn Voltage (I <sub>E</sub> = 100 μA)		V(BR)EBO	7	7.8	_	V
DC Current Gain (I <sub>C</sub> =	2 mA, V <sub>CE</sub> = 5 V)		hFE	_	400	_	_
Collector–Emitter Capacitance (f = 1 MHz, V <sub>CE</sub> = 0)		C <sub>CE</sub>	_	7	_	pF	
Collector-Base Capac	itance (f = 1 MHz, V <sub>CB</sub> = 0)		ССВ	_	19	_	pF
Emitter-Base Capacita	ance (f = 1 MHz, V <sub>EB</sub> = 0)		C <sub>EB</sub>	_	9	_	pF
COUPLED			•				
Output Collector Curre (IF = 10 mA, VCE =		T <sub>A</sub> = 25°C T <sub>A</sub> = -55°C T <sub>A</sub> = 100°C	I <sub>C</sub> (CTR) <sup>(2)</sup>	10 (100) 4 (40) 4 (40)	30 (300) — —		mA (%)
Collector–Emitter Satu	ration Voltage ( $I_C = 0.5 \text{ mA}, I_F$	= 10 mA)	V <sub>CE(sat)</sub>	_	0.14	0.3	V
Turn-On Time			t <sub>on</sub>	_	7.5	10	μs
Turn-Off Time	$(I_C = 2 \text{ mA}, V_{CC})$	= 10 V,	toff	_	5.7	10	
Rise Time	$R_{L} = 100 \Omega)(3)$		t <sub>r</sub>	_	3.2		
Fall Time			t <sub>f</sub>	_	4.7		
Isolation Voltage (f = 60 Hz, t = 1 sec)		VISO	7500	1	1	Vac(pk)	
Isolation Current(4) $(V_{I-O} = 3550 \text{ Vpk})$ 4N35 $(V_{I-O} = 2500 \text{ Vpk})$ 4N36 $(V_{I-O} = 1500 \text{ Vpk})$ 4N37		liso	_ _ _	8	100 100 100	μА	
Isolation Resistance (V = 500 V) <sup>(4)</sup>		R <sub>ISO</sub>	10 <sup>11</sup>	_	_	Ω	
Isolation Capacitance	$(V = 0 V, f = 1 MHz)^{(4)}$	Isolation Capacitance (V = 0 V, f = 1 MHz) <sup>(4)</sup>		_	0.2	2	pF

<sup>1.</sup> Always design to the specified minimum/maximum electrical limits (where applicable).

<sup>2.</sup> Current Transfer Ratio (CTR) =  $I_C/I_F \times 100\%$ .

<sup>3.</sup> For test circuit setup and waveforms, refer to Figure 11.

<sup>4.</sup> For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

### **TYPICAL CHARACTERISTICS**

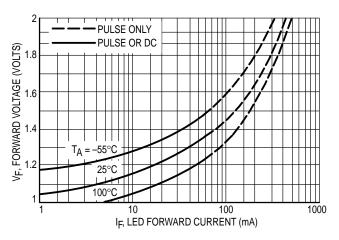


Figure 1. LED Forward Voltage versus Forward Current

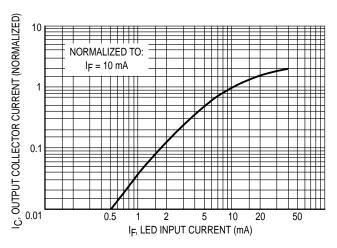


Figure 2. Output Current versus Input Current

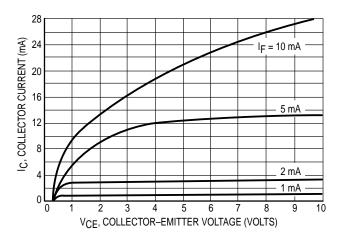


Figure 3. Collector Current versus Collector–Emitter Voltage

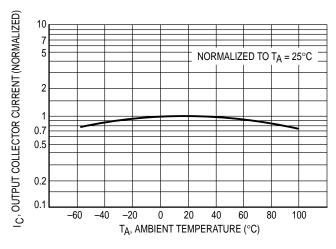


Figure 4. Output Current versus Ambient Temperature

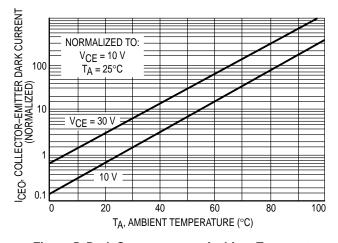


Figure 5. Dark Current versus Ambient Temperature

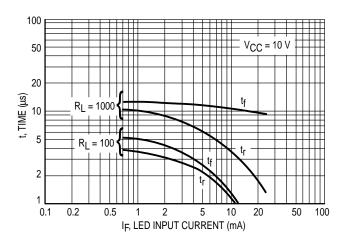


Figure 6. Rise and Fall Times (Typical Values)

### 4N35 4N36 4N37

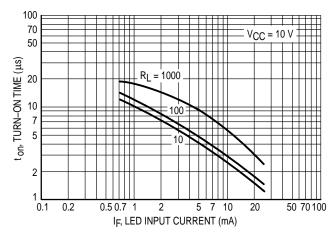


Figure 7. Turn-On Switching Times

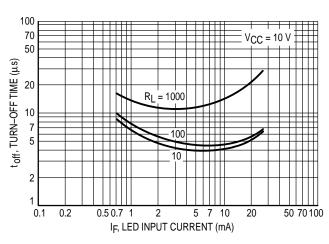


Figure 8. Turn-Off Switching Times

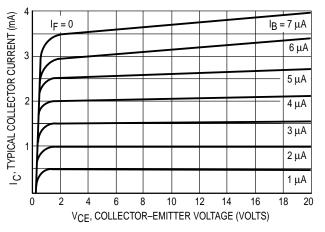


Figure 9. DC Current Gain (Detector Only)

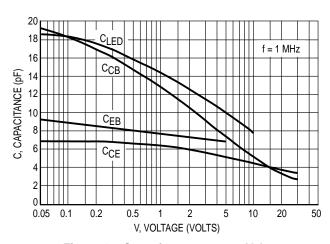


Figure 10. Capacitances versus Voltage

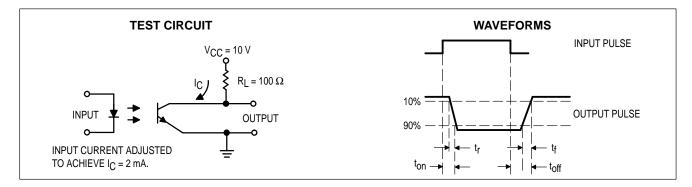
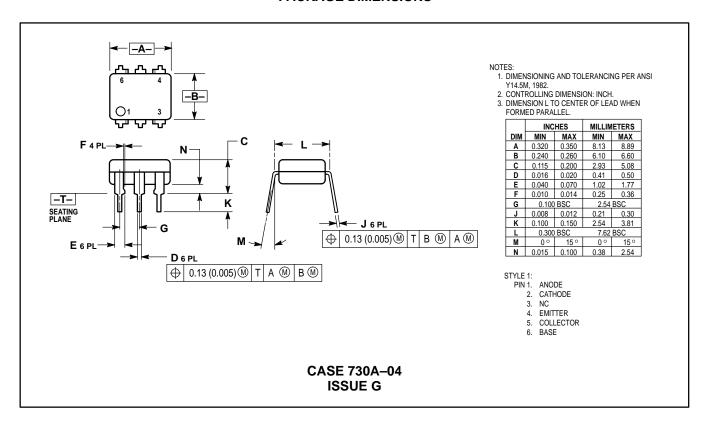
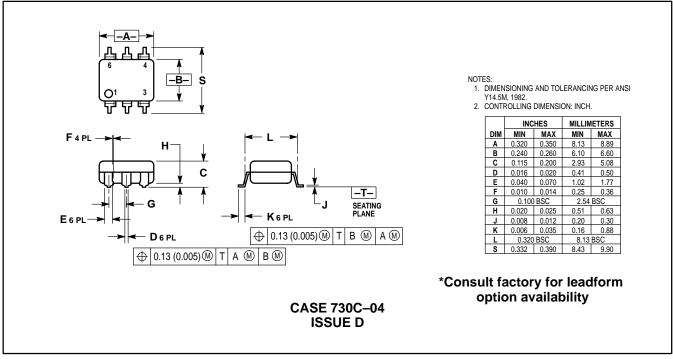


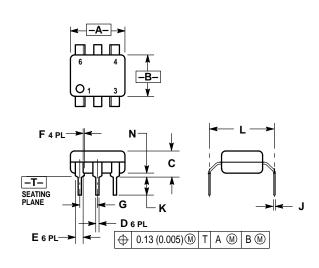
Figure 11. Switching Time Test Circuit and Waveforms

### PACKAGE DIMENSIONS





### 4N35 4N36 4N37



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
   DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.320	0.350	8.13	8.89
В	0.240	0.260	6.10	6.60
С	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
Е	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
J	0.008	0.012	0.21	0.30
K	0.100	0.150	2.54	3.81
L	0.400	0.425	10.16	10.80
N	0.015	0.040	0.38	1.02

\*Consult factory for leadform option availability

CASE 730D-05 **ISSUE D** 

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